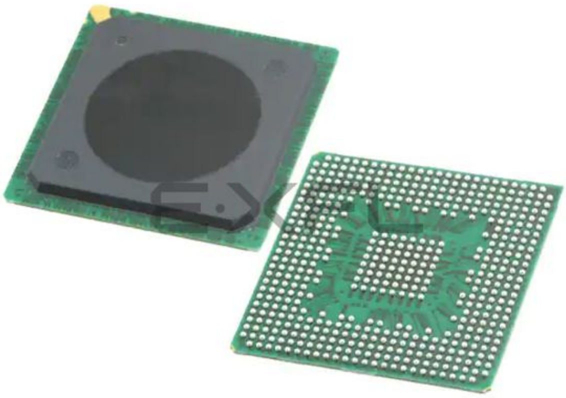

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300c2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	516-BBGA
Supplier Device Package	516-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8323vraddc

2.1.2 Power Supply Voltage Specification

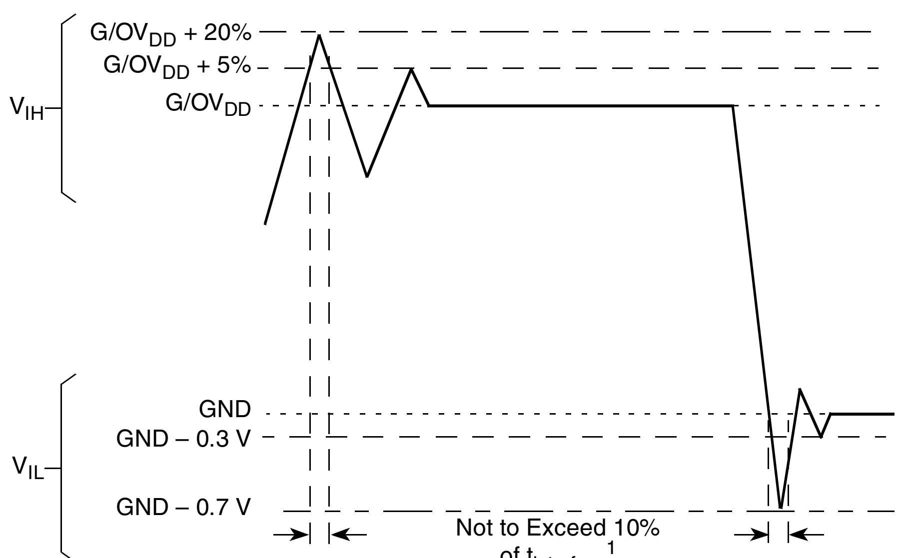
Table 2 provides the recommended operating conditions for the MPC8323E. Note that these values are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 2. Recommended Operating Conditions[3]

Characteristic	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V_{DD}	1.0 V ± 50 mV	V	1
PLL supply voltage	AV_{DD}	1.0 V ± 50 mV	V	1
DDR1 and DDR2 DRAM I/O voltage	GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	1
PCI, local bus, DUART, system control and power management, I^2C, SPI, and JTAG I/O voltage	OV_{DD}	3.3 V ± 300 mV	V	1
Junction temperature	T_A/T_J	0 to 105	°C	2

Note:
1. GV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
2. Minimum temperature is specified with T_A; maximum temperature is specified with T_J.
3. All IO pins should be interfaced with peripherals operating at same voltage level.
4. This voltage is the input to the filter discussed in Section 24.2, "PLL Power Supply Filtering" and not necessarily the voltage at the AVDD pin, which may be reduced due to voltage drop across the filter.

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8323E



Note:
1. $t_{interface}$ refers to the clock period associated with the bus clock interface.

Figure 2. Overshoot/Undershoot Voltage for GV_{DD}/OV_{DD}

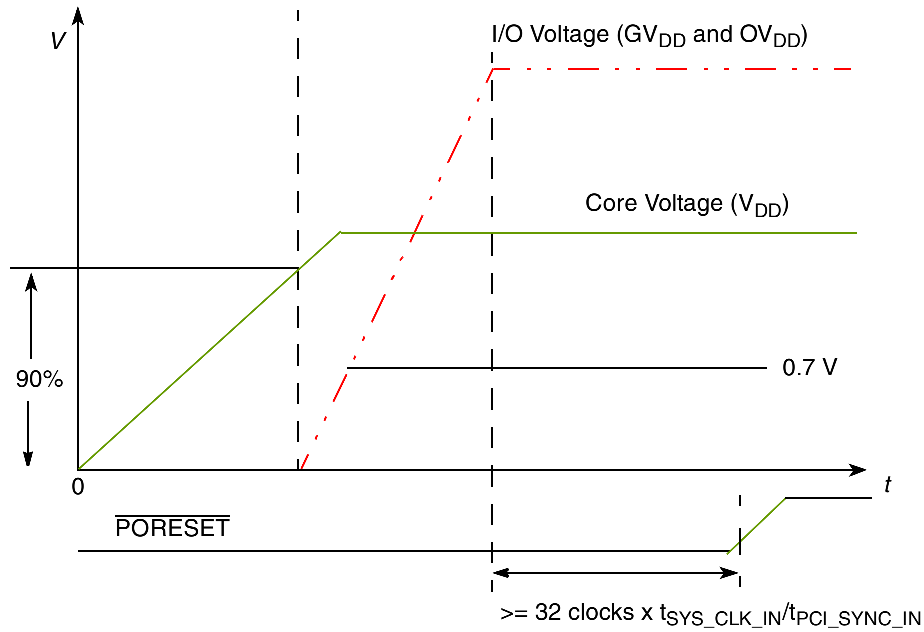


Figure 3. MPC8323E Power-Up Sequencing Example

3 Power Characteristics

The estimated typical power dissipation for this family of MPC8323E devices is shown in Table 5.

Table 5. MPC8323E Power Dissipation

CSB Frequency (MHz)	QUICC Engine Frequency (MHz)	Core Frequency (MHz)	Typical	Maximum	Unit	Notes
133	200	266	0.74	1.48	W	1, 2, 3
133	200	333	0.78	1.62	W	1, 2, 3

Notes:

1. The values do not include I/O supply power (OV_{DD} and GV_{DD}) or AV_{DD}. For I/O power values, see Table 6.
2. Typical power is based on a nominal voltage of V_{DD} = 1.0 V, ambient temperature, and the core running a Dhrystone benchmark application. The measurements were taken on the MPC8323MDS evaluation board using WC process silicon.
3. Maximum power is based on a voltage of V_{DD} = 1.07 V, WC process, a junction T_J = 110°C, and an artificial smoke test.

Table 6 shows the estimated typical I/O power dissipation for the device.

Table 6. Estimated Typical I/O Power Dissipation

Interface	Parameter	GV_{DD} (1.8 V)	GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	Unit	Comments
DDR I/O 65% utilization 2.5 V R_s = 20 Ω R_t = 50 Ω 1 pair of clocks	266 MHz, 1 × 32 bits	0.212	0.367	—	W	—

Table 13. DDR2 SDRAM Capacitance for Dn_GV$_{DD}$(typ) = 1.8 V

Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. Dn_GV$_{DD}$ = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25 °C, V_{OUT} = Dn_GV$_{DD}$ ÷ 2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR1 SDRAM component(s) of the MPC8323E when Dn_GV$_{DD}$(typ) = 2.5 V.

Table 14. DDR1 SDRAM DC Electrical Characteristics for Dn_GV$_{DD}$(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	Dn_GV$_{DD}$	2.375	2.625	V	1
I/O reference voltage	MVREFn_{REF}	0.49 × Dn_GV$_{DD}$	0.51 × Dn_GV$_{DD}$	V	2
I/O termination voltage	V_{TT}	MVREFn_{REF} – 0.04	MVREFn_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MVREFn_{REF} + 0.15	Dn_GV$_{DD}$ + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MVREFn_{REF} – 0.15	V	—
Output leakage current	I_{OZ}	–9.9	–9.9	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. Dn_GV$_{DD}$ is expected to be within 50 mV of the DRAM Dn_GV$_{DD}$ at all times.
2. MVREFn_{REF} is expected to be equal to 0.5 × Dn_GV$_{DD}$, and to track Dn_GV$_{DD}$ DC variations as measured at the receiver. Peak-to-peak noise on MVREFn_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MVREFn_{REF}. This rail should track variations in the DC level of MVREFn_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ Dn_GV$_{DD}$.

Table 15 provides the DDR1 capacitance Dn_GV$_{DD}$(typ) = 2.5 V.

Table 15. DDR1 SDRAM Capacitance for Dn_GV$_{DD}$(typ) = 2.5 V Interface

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ,DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. Dn_GV$_{DD}$ = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25° C, V_{OUT} = Dn_GV$_{DD}$ ÷ 2, V_{OUT} (peak-to-peak) = 0.2 V.

Figure 4 shows the input timing diagram for the DDR controller.

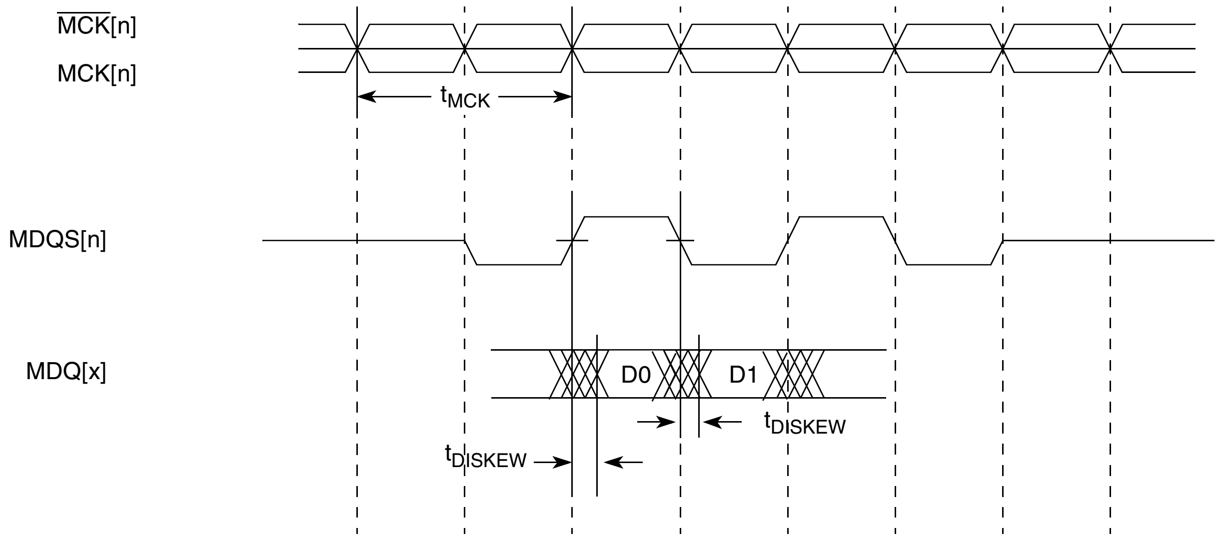


Figure 4. DDR Input Timing Diagram

6.2.2 DDR1 and DDR2 SDRAM Output AC Timing Specifications

Table 19 provides the output AC timing specifications for the DDR1 and DDR2 SDRAM interfaces.

Table 19. DDR1 and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with D*n*_GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MCK cycle time, (MCK/$\overline{MCK}$ crossing)	t_{MCK}	7.5	10	ns	2
ADDR/CMD output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHAS}	 2.5 3.5	 — —	ns	3
ADDR/CMD output hold with respect to MCK 266 MHz 200 MHz	t_{DDKHAX}	 2.5 3.5	 — —	ns	3
$\overline{MCS}$ output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHCS}	 2.5 3.5	 — —	ns	3
$\overline{MCS}$ output hold with respect to MCK 266 MHz 200 MHz	t_{DDKHCX}	 2.5 3.5	 — —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4

Table 19. DDR1 and DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with D*n*_GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQ/MDM output setup with respect to MDQS 266 MHz 200 MHz	t_{DDKHDS}, t_{DDKLDS}	 0.9 1.0	 — —	ns	5
MDQ/MDM output hold with respect to MDQS 266 MHz 200 MHz	t_{DDKHDX}, t_{DDKLDX}	 1100 1200	 — —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the Clock Control register is set to adjust the memory clocks by 1/2 applied cycle.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8323E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK(n) at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

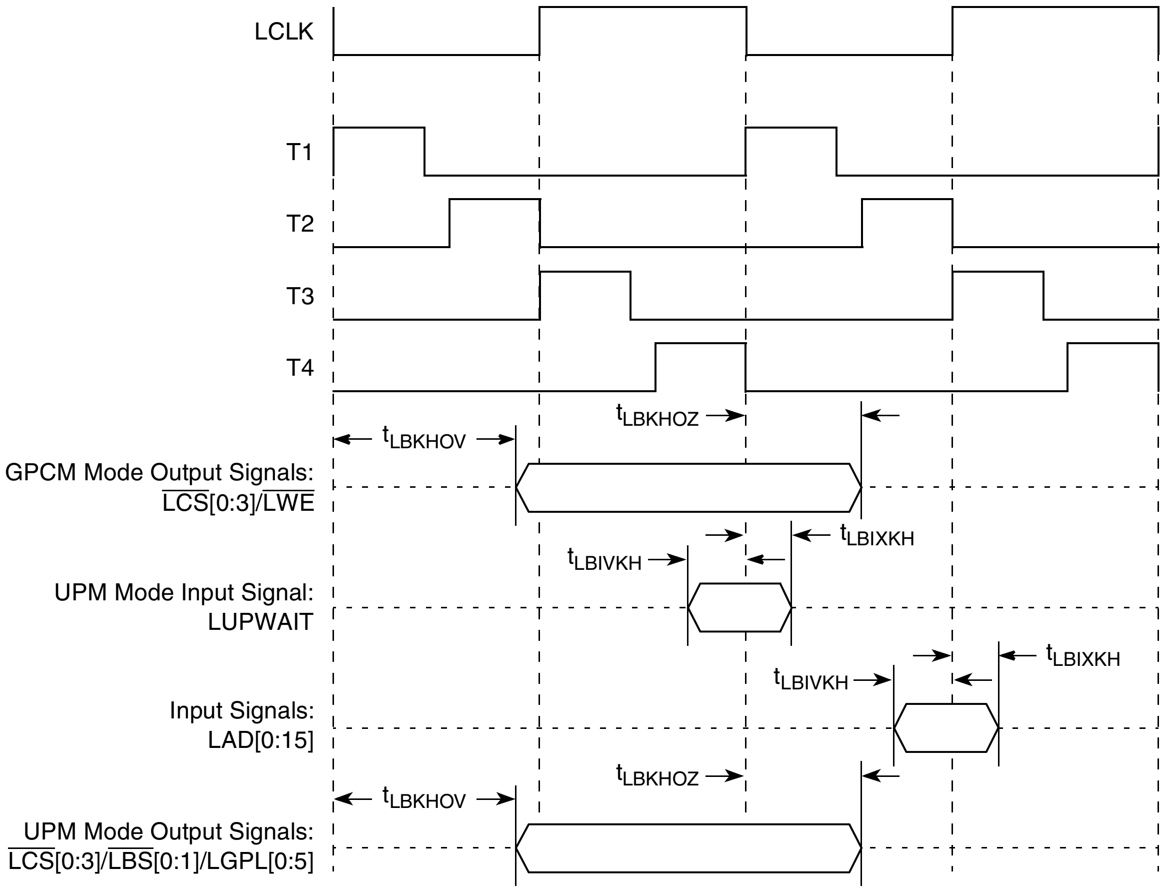


Figure 17. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4

10 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1™ (JTAG) interface of the MPC8323E.

10.1 JTAG DC Electrical Characteristics

Table 31 provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8323E.

Table 31. JTAG Interface DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.5	OV_{DD} + 0.3	V

16 SPI

This section describes the DC and AC electrical specifications for the SPI of the MPC8323E.

16.1 SPI DC Electrical Characteristics

Table 44 provides the DC electrical characteristics for the MPC8323E SPI.

Table 44. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = –6.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 6.0$ mA	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2$ mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	±5	μA

16.2 SPI AC Timing Specifications

Table 45 and provide the SPI input and output AC timing specifications.

Table 45. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOV}	0.5	6	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOV}	2	8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	6	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

Figure 30 provides the AC test load for the SPI.

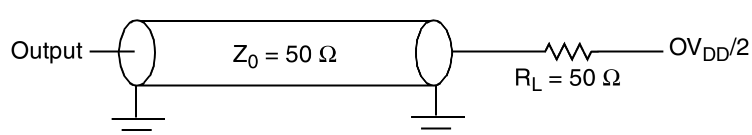
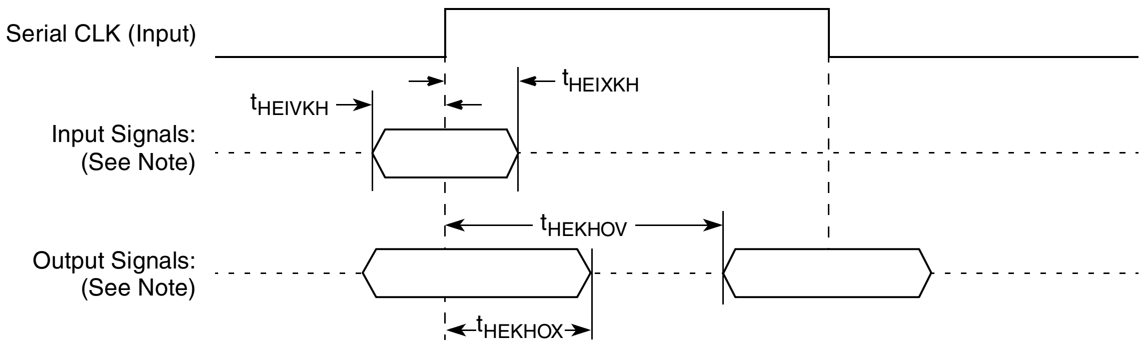


Figure 30. SPI AC Test Load

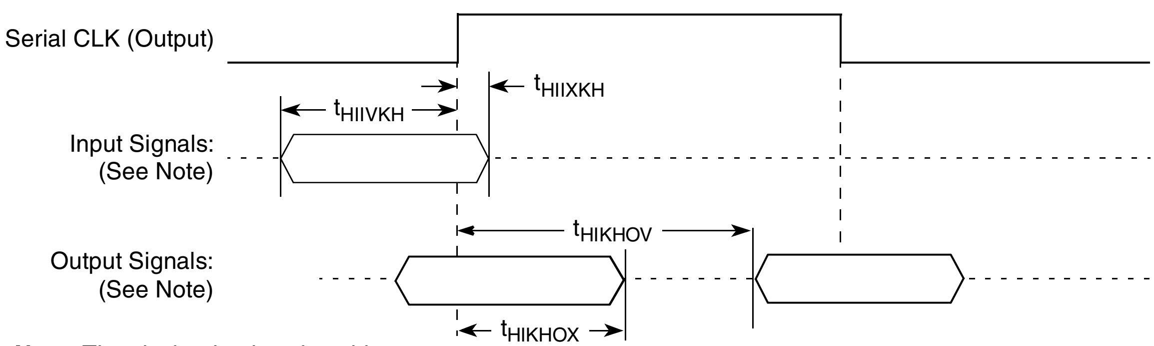
Figure 39 shows the timing with external clock.



Note: The clock edge is selectable.

Figure 39. AC Timing (External Clock) Diagram

Figure 40 shows the timing with internal clock.



Note: The clock edge is selectable.

Figure 40. AC Timing (Internal Clock) Diagram

20 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8323E.

20.1 USB DC Electrical Characteristics

Table 53 provides the DC electrical characteristics for the USB interface.

Table 53. USB DC Electrical Characteristics[1]

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±5	µA

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

20.2 USB AC Electrical Specifications

Table 54 describes the general timing parameters of the USB interface of the MPC8323E.

Table 54. USB General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	20.83	—	ns	Full speed 48 MHz
USB clock cycle time	t_{USCK}	166.67	—	ns	Low speed 6 MHz
Skew between TXP and TXN	t_{USTSPN}	—	5	ns	—
Skew among RXP, RXN, and RXD	$t_{USRSPND}$	—	10	ns	Full speed transitions
Skew among RXP, RXN, and RXD	t_{USRPND}	—	100	ns	Low speed transitions

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(state)(signal)}}$ for receive signals and $t_{\text{(first two letters of functional block)(state)(signal)}}$ for transmit signals. For example, $t_{USRSPND}$ symbolizes USB timing (US) for the USB receive signals skew (RS) among RXP, RXN, and RXD (PND). Also, t_{USTSPN} symbolizes USB timing (US) for the USB transmit signals skew (TS) between TXP and TXN (PN).
2. Skew measurements are done at OV_{DD}/2 of the rising or falling edge of the signals.

Figure 41 provide the AC test load for the USB.

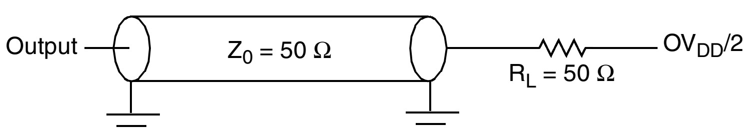


Figure 41. USB AC Test Load

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LCS1	AB25	O	OV_{DD}	4
LCS2	AA23	O	OV_{DD}	4
LCS3	AA24	O	OV_{DD}	4
LWE0	Y23	O	OV_{DD}	4
LWE1	W25	O	OV_{DD}	4
LBCTL	V25	O	OV_{DD}	4
LALE	V24	O	OV_{DD}	7
CFG_RESET_SOURCE[0]/LSDA10/LGPL0	L23	IO	OV_{DD}	—
CFG_RESET_SOURCE[1]/LSDWE/LGPL1	K23	IO	OV_{DD}	—
LSDRAS/LGPL2/LOE	J23	O	OV_{DD}	4
CFG_RESET_SOURCE[2]/LSDCAS/LGPL3	H23	IO	OV_{DD}	—
LGPL4/LGTA/LUPWAIT/LPBSE	G23	IO	OV_{DD}	4, 8
LGPL5	AC22	O	OV_{DD}	4
LCLK0	Y24	O	OV_{DD}	7
LCLK1	Y25	O	OV_{DD}	7
DUART				
UART_SOUT1/MSRCID0 (DDR ID)/LSRCID0	G1	IO	OV_{DD}	—
UART_SIN1/MSRCID1 (DDR ID)/LSRCID1	G2	IO	OV_{DD}	—
UART_CTS1/MSRCID2 (DDR ID)/LSRCID2	H3	IO	OV_{DD}	—
UART_RTS1/MSRCID3 (DDR ID)/LSRCID3	K3	IO	OV_{DD}	—
UART_SOUT2/MSRCID4 (DDR ID)/LSRCID4	H2	IO	OV_{DD}	—
UART_SIN2/MDVAL (DDR ID)/LDVAL	H1	IO	OV_{DD}	—
UART_CTS2	J3	IO	OV_{DD}	—
UART_RTS2	K4	IO	OV_{DD}	—
I^2C interface				
IIC_SDA/CKSTOP_OUT	AE24	IO	OV_{DD}	2
IIC_SCL/CKSTOP_IN	AF24	IO	OV_{DD}	2
Programmable Interrupt Controller				
MCP_OUT	AD25	O	OV_{DD}	—
IRQ0/MCP_IN	AD26	I	OV_{DD}	—
IRQ1	K1	IO	OV_{DD}	—
IRQ2	K2	I	OV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{IRQ3}}$	J2	I	OV_{DD}	—
$\overline{\text{IRQ4}}$	J1	I	OV_{DD}	—
$\overline{\text{IRQ5}}$	AE26	I	OV_{DD}	—
$\overline{\text{IRQ6}}$/$\overline{\text{CKSTOP\_OUT}}$	AE25	IO	OV_{DD}	—
$\overline{\text{IRQ7}}$/$\overline{\text{CKSTOP\_IN}}$	AF25	I	OV_{DD}	—
$\overline{\text{CFG\_CLKIN\_DIV}}$	F1	I	OV_{DD}	—
CFG_LBIU_MUX_EN	M23	I	OV_{DD}	—
JTAG				
TCK	W26	I	OV_{DD}	—
TDI	Y26	I	OV_{DD}	4
TDO	AA26	O	OV_{DD}	3
TMS	AB26	I	OV_{DD}	4
$\overline{\text{TRST}}$	AC26	I	OV_{DD}	4
TEST				
TEST_MODE	N23	I	OV_{DD}	6
PMC				
$\overline{\text{QUIESCE}}$	T23	O	OV_{DD}	—
System Control				
$\overline{\text{HRESET}}$	AC23	IO	OV_{DD}	1
$\overline{\text{PORESET}}$	AD23	I	OV_{DD}	—
$\overline{\text{SRESET}}$	AD24	IO	OV_{DD}	2
Clocks				
CLKIN	R3	I	OV_{DD}	—
$\overline{\text{CLKIN}}$	P4	O	OV_{DD}	—
PCI_SYNC_OUT	V1	O	OV_{DD}	3
RTC_PIT_CLOCK	U23	I	OV_{DD}	—
PCI_SYNC_IN/PCI_CLK	V2	I	OV_{DD}	—
PCI_CLK0/clkpd_cerisc1_ipg_clkout/DPTC_OSC	T3	O	OV_{DD}	—
PCI_CLK1/clkpd_half_cemb4ucc1_ipg_clkout/ CLOCK_XLB_CLOCK_OUT	U2	O	OV_{DD}	—
PCI_CLK2/clkpd_third_cesog_ipg_clkout/ cecl_ipg_ce_clock	R4	O	OV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_AD20	AB2	IO	OV_{DD}	—
PCI_AD21	Y4	IO	OV_{DD}	—
PCI_AD22	AC1	IO	OV_{DD}	—
PCI_AD23	AA3	IO	OV_{DD}	—
PCI_AD24	AA4	IO	OV_{DD}	—
PCI_AD25	AD1	IO	OV_{DD}	—
PCI_AD26	AD2	IO	OV_{DD}	—
PCI_AD27	AB3	IO	OV_{DD}	—
PCI_AD28	AB4	IO	OV_{DD}	—
PCI_AD29	AE1	IO	OV_{DD}	—
PCI_AD30	AC3	IO	OV_{DD}	—
PCI_AD31	AC4	IO	OV_{DD}	—
PCI_C_$\overline{\text{BE0}}$	M4	IO	OV_{DD}	—
PCI_C_$\overline{\text{BE1}}$	T4	IO	OV_{DD}	—
PCI_C_$\overline{\text{BE2}}$	Y3	IO	OV_{DD}	—
PCI_C_$\overline{\text{BE3}}$	AC2	IO	OV_{DD}	—
PCI_PAR	U3	IO	OV_{DD}	—
$\overline{\text{PCI\_FRAME}}$	W1	IO	OV_{DD}	5
$\overline{\text{PCI\_TRDY}}$	W4	IO	OV_{DD}	5
$\overline{\text{PCI\_IRDY}}$	W2	IO	OV_{DD}	5
$\overline{\text{PCI\_STOP}}$	V4	IO	OV_{DD}	5
$\overline{\text{PCI\_DEVSEL}}$	W3	IO	OV_{DD}	5
PCI_IDSEL	P2	I	OV_{DD}	—
$\overline{\text{PCI\_SERR}}$	U4	IO	OV_{DD}	5
$\overline{\text{PCI\_PERR}}$	V3	IO	OV_{DD}	5
$\overline{\text{PCI\_REQ0}}$	AD4	IO	OV_{DD}	—
$\overline{\text{PCI\_REQ1}}$/CPCI_HS_ES	AE3	I	OV_{DD}	—
$\overline{\text{PCI\_REQ2}}$	AF3	I	OV_{DD}	—
$\overline{\text{PCI\_GNT0}}$	AD3	IO	OV_{DD}	—
$\overline{\text{PCI\_GNT1}}$/CPCI_HS_LED	AE4	O	OV_{DD}	—
$\overline{\text{PCI\_GNT2}}$/CPCI_HS_ENUM	AF4	O	OV_{DD}	—
M66EN	L4	I	OV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPIO_PB17/BRGO1/CE_EXT_REQ1	D10	IO	OV_{DD}	—
GPIO_PB18/Enet4_TXD[0]/SER4_TXD[0]/ TDMD_TXD[0]	C10	IO	OV_{DD}	—
GPIO_PB19/Enet4_TXD[1]/SER4_TXD[1]/ TDMD_TXD[1]	C9	IO	OV_{DD}	—
GPIO_PB20/Enet4_TXD[2]/SER4_TXD[2]/ TDMD_TXD[2]	D8	IO	OV_{DD}	—
GPIO_PB21/Enet4_TXD[3]/SER4_TXD[3]/ TDMD_TXD[3]	C8	IO	OV_{DD}	—
GPIO_PB22/Enet4_RXD[0]/SER4_RXD[0]/ TDMD_RXD[0]	C15	IO	OV_{DD}	—
GPIO_PB23/Enet4_RXD[1]/SER4_RXD[1]/ TDMD_RXD[1]	C14	IO	OV_{DD}	—
GPIO_PB24/Enet4_RXD[2]/SER4_RXD[2]/ TDMD_RXD[2]	D13	IO	OV_{DD}	—
GPIO_PB25/Enet4_RXD[3]/SER4_RXD[3]/ TDMD_RXD[3]	C13	IO	OV_{DD}	—
GPIO_PB26/Enet4_RX_ER/SER4_CD/TDMD_REQ	C12	IO	OV_{DD}	—
GPIO_PB27/Enet4_TX_ER/TDMD_CLKO	D11	IO	OV_{DD}	—
GPIO_PB28/Enet4_RX_DV/SER4_CTS/ TDMD_RSYNC	D12	IO	OV_{DD}	—
GPIO_PB29/Enet4_COL/RXD[4]/SER4_RXD[4]/ TDMD_STROBE	D7	IO	OV_{DD}	—
GPIO_PB30/Enet4_TX_EN/SER4_RTS/ TDMD_TSYNC	C11	IO	OV_{DD}	—
GPIO_PB31/Enet4_CRS/SDET	C7	IO	OV_{DD}	—
GPIO_PC0/UPC1_TxDATA[0]/SER5_TXD[0]	A18	IO	OV_{DD}	—
GPIO_PC1/UPC1_TxDATA[1]/SER5_TXD[1]	A19	IO	OV_{DD}	—
GPIO_PC2/UPC1_TxDATA[2]/SER5_TXD[2]	B18	IO	OV_{DD}	—
GPIO_PC3/UPC1_TxDATA[3]/SER5_TXD[3]	B19	IO	OV_{DD}	—
GPIO_PC4/UPC1_TxDATA[4]	A24	IO	OV_{DD}	—
GPIO_PC5/UPC1_TxDATA[5]	B24	IO	OV_{DD}	—
GPIO_PC6/UPC1_TxDATA[6]	A23	IO	OV_{DD}	—
GPIO_PC7/UPC1_TxDATA[7]	B26	IO	OV_{DD}	—
GPIO_PC8/UPC1_RxDATA[0]/SER5_RXD[0]	A21	IO	OV_{DD}	—
GPIO_PC9/UPC1_RxDATA[1]/SER5_RXD[1]	B20	IO	OV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPIO_PC10/UPC1_RxDATA[2]/SER5_RXD[2]	B21	IO	OV_{DD}	—
GPIO_PC11/UPC1_RxDATA[3]/SER5_RXD[3]	A20	IO	OV_{DD}	—
GPIO_PC12/UPC1_RxDATA[4]	D19	IO	OV_{DD}	—
GPIO_PC13/UPC1_RxDATA[5]/LSRCID0	C18	IO	OV_{DD}	—
GPIO_PC14/UPC1_RxDATA[6]/LSRCID1	D18	IO	OV_{DD}	—
GPIO_PC15/UPC1_RxDATA[7]/LSRCID2	A25	IO	OV_{DD}	—
GPIO_PC16/UPC1_TxADDR[0]	C21	IO	OV_{DD}	—
GPIO_PC17/UPC1_TxADDR[1]/LSRCID3	D22	IO	OV_{DD}	—
GPIO_PC18/UPC1_TxADDR[2]/LSRCID4	C23	IO	OV_{DD}	—
GPIO_PC19/UPC1_TxADDR[3]/LDVAL	D23	IO	OV_{DD}	—
GPIO_PC20/UPC1_RxADDR[0]	C17	IO	OV_{DD}	—
GPIO_PC21/UPC1_RxADDR[1]	D17	IO	OV_{DD}	—
GPIO_PC22/UPC1_RxADDR[2]	C16	IO	OV_{DD}	—
GPIO_PC23/UPC1_RxADDR[3]	D16	IO	OV_{DD}	—
GPIO_PC24/UPC1_RxSOC/SER5_CD	A16	IO	OV_{DD}	—
GPIO_PC25/UPC1_RxCLAV	D20	IO	OV_{DD}	—
GPIO_PC26/UPC1_RxPRTY/CE_EXT_REQ2	E23	IO	OV_{DD}	—
GPIO_PC27/UPC1_RxEN	B17	IO	OV_{DD}	—
GPIO_PC28/UPC1_TxSOC	B22	IO	OV_{DD}	—
GPIO_PC29/UPC1_TxCLAV/SER5_CTS	A17	IO	OV_{DD}	—
GPIO_PC30/UPC1_TxPRTY	A22	IO	OV_{DD}	—
GPIO_PC31/UPC1_TxEN/SER5_RTS	C20	IO	OV_{DD}	—
GPIO_PD0/SPIMOSI	A2	IO	OV_{DD}	—
GPIO_PD1/SPIMISO	B2	IO	OV_{DD}	—
GPIO_PD2/SPICLK	B3	IO	OV_{DD}	—
GPIO_PD3/SPISEL	A3	IO	OV_{DD}	—
GPIO_PD4/SPI_MDIO/CE_MUX_MDIO	A4	IO	OV_{DD}	—
GPIO_PD5/SPI_MDC/CE_MUX_MDC	B4	IO	OV_{DD}	—
GPIO_PD6/CLK8/BRGO16/CE_EXT_REQ3	F24	IO	OV_{DD}	—
GPIO_PD7/GTM1_TIN1/GTM2_TIN2/CLK5	G24	IO	OV_{DD}	—
GPIO_PD8/$\overline{\mathrm{GTM1\_TGATE1}}$/$\overline{\mathrm{GTM2\_TGATE2}}$/CLK6	H24	IO	OV_{DD}	—
GPIO_PD9/$\overline{\mathrm{GTM1\_TOUT1}}$	D24	IO	OV_{DD}	—

Table 57. Operating Frequencies for PBGA (continued)

Characteristic[1]	Max Operating Frequency	Unit
DDR1/DDR2 memory bus frequency (MCLK)[2]	133	MHz
Local bus frequency (LCLK*n*)[3]	66	MHz
PCI input frequency (CLKIN or PCI_CLK)	66	MHz

[1] The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.
[2] The DDR1/DDR2 data rate is 2× the DDR1/DDR2 memory bus frequency.
[3] The local bus frequency is 1/2, 1/4, or 1/8 of the *lb_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWL[LBCM]).

22.4 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 58 shows the multiplication factor encodings for the system PLL.

NOTE

System PLL VCO frequency = 2 × (CSB frequency) × (System PLL VCO divider).

The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 300–600 MHz.

Table 58. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	Reserved
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111–1111	Reserved

As described in Section 22, “Clocking,” the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the $\overline{\text{CFG\_CLKIN\_DIV}}$ configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 59 shows the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 59. CSB Frequency Options

CFG_CLKIN_DIV_B at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio [2]	Input Clock Frequency (MHz)[2]		
			25	33.33	66.67
			csb_clk Frequency (MHz)		
High	0010	2 : 1			133
High	0011	3 : 1		100	
High	0100	4 : 1	100	133	
High	0101	5 : 1	125		
High	0110	6 : 1			
High	0111	7 : 1			
High	1000	8 : 1			
High	1001	9 : 1			
High	1010	10 : 1			
High	1011	11 : 1			
High	1100	12 : 1			
High	1101	13 : 1			
High	1110	14 : 1			
High	1111	15 : 1			
High	0000	16 : 1			
Low	0010	2 : 1			133
Low	0011	3 : 1		100	
Low	0100	4 : 1		133	
Low	0101	5 : 1			
Low	0110	6 : 1			
Low	0111	7 : 1			
Low	1000	8 : 1			
Low	1001	9 : 1			
Low	1010	10 : 1			
Low	1011	11 : 1			
Low	1100	12 : 1			
Low	1101	13 : 1			
Low	1110	14 : 1			
Low	1111	15 : 1			
Low	0000	16 : 1			

1 CFG_CLKIN_DIV_B is only used for host mode; CLKIN must be tied low and CFG_CLKIN_DIV_B must be pulled up (high) in agent mode.

2 CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

22.7 Suggested PLL Configurations

To simplify the PLL configurations, the MPC8323E might be separated into two clock domains. The first domain contain the CSB PLL and the core PLL. The core PLL is connected serially to the CSB PLL, and has the csb_clk as its input clock. The second clock domain has the QUICC Engine PLL. The clock domains are independent, and each of their PLLs are configured separately. Both of the domains has one common input clock. Table 63 shows suggested PLL configurations for 33, 25, and 66 MHz input clocks.

Table 63. Suggested PLL Configurations

Conf No.	SPMF	Core PLL	CEMF	CEDF	Input Clock Frequency (MHz)	CSB Frequency (MHz)	Core Frequency (MHz)	QUICC Engine Frequency (MHz)
1	0100	0000100	0110	0	33.33	133.33	266.66	200
2	0100	0000101	1000	0	25	100	250	200
3	0010	0000100	0011	0	66.67	133.33	266.66	200
4	0100	0000101	0110	0	33.33	133.33	333.33	200
5	0101	0000101	1000	0	25	125	312.5	200
6	0010	0000101	0011	0	66.67	133.33	333.33	200

23 Thermal

This section describes the thermal specifications of the MPC8323E.

23.1 Thermal Characteristics

Table 64 provides the package thermal characteristics for the 516 27 × 27 mm PBGA of the MPC8323E.

Table 64. Package Thermal Characteristics for PBGA

Characteristic	Board type	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection	Single-layer board (1s)	$R_{\theta JA}$	28	°C/W	1, 2
Junction-to-ambient natural convection	Four-layer board (2s2p)	$R_{\theta JA}$	21	°C/W	1, 2, 3
Junction-to-ambient (@200 ft/min)	Single-layer board (1s)	$R_{\theta JMA}$	23	°C/W	1, 3
Junction-to-ambient (@200 ft/min)	Four-layer board (2s2p)	$R_{\theta JMA}$	18	°C/W	1, 3
Junction-to-board	—	$R_{\theta JB}$	13	°C/W	4
Junction-to-case	—	$R_{\theta JC}$	9	°C/W	5

(edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_B + (R_{\theta JB} \times P_D)$$

where:

T_J = junction temperature (°C)

T_B = board temperature at the package perimeter (°C)

$R_{\theta JB}$ = junction-to-board thermal resistance (°C/W) per JESD51-8

P_D = power dissipation in package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

23.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the thermal characterization parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)

T_T = thermocouple temperature on top of package (°C)

Ψ_{JT} = thermal characterization parameter (°C/W)

P_D = power dissipation in package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

23.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

In some application environments, a heat sink is required to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_C = case temperature of the package (°C)

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

P_D = power dissipation (W)

24 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8323E.

24.1 System Clocking

The MPC8323E includes three PLLs.

- The system PLL ($AV_{DD}2$) generates the system clock from the externally supplied CLKIN input. The frequency ratio between the system and CLKIN is selected using the system PLL ratio configuration bits as described in Section 22.4, "System PLL Configuration."
- The e300 core PLL ($AV_{DD}3$) generates the core clock as a slave to the system clock. The frequency ratio between the e300 core clock and the system clock is selected using the e300 PLL ratio configuration bits as described in Section 22.5, "Core PLL Configuration."
- The QUICC Engine PLL ($AV_{DD}1$) which uses the same reference as the system PLL. The QUICC Engine block generates or uses external sources for all required serial interface clocks.

24.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins. The voltage level at each $AV_{DD}n$ pin should always be equivalent to V_{DD}, and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide five independent filter circuits as illustrated in Figure 44, one to each of the five AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

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